

# **NPN RF Transistor**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	V
Ic	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	N	Units	
		PN918	*MMBT918	
P <sub>D</sub>	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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# **NPN RF Transistor**

# (continued)

<b>Electrical Characteristics</b>	
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Electri	cal Characteristics TA = 25	<b>S</b> TA = 25°C unless otherwise noted			
Symbol	Parameter	Test Conditions	Min	Max	Units

### **OFF CHARACTERISTICS**

V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 1.0 \ \mu A, \ I_{E} = 0$	30		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	3.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		0.01	μΑ
		V <sub>CB</sub> = 15 V, T <sub>A</sub> = 150°C		1.0	μA

# **ON CHARACTERISTICS**

h <sub>FE</sub>	DC Current Gain	$I_{C}$ = 3.0 mA, $V_{CE}$ = 1.0 V	20		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		1.0	V

# SMALL SIGNAL CHARACTERISTICS

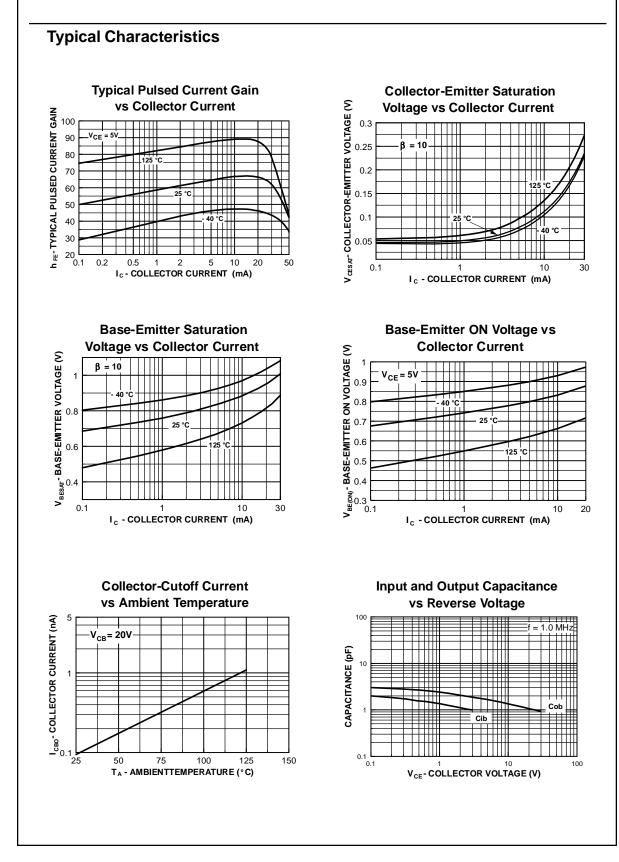
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C} = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	600		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ $V_{CB} = 0, I_E = 0, f = 1.0 \text{ MHz}$		1.7 3.0	pF pF
C <sub>ibo</sub>	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		2.0	pF
NF	Noise Figure	$I_{C} = 1.0 \text{ mA}, V_{CE} = 6.0 \text{ V}, R_{G} = 400\Omega, f = 60 \text{ MHz}$		6.0	dB

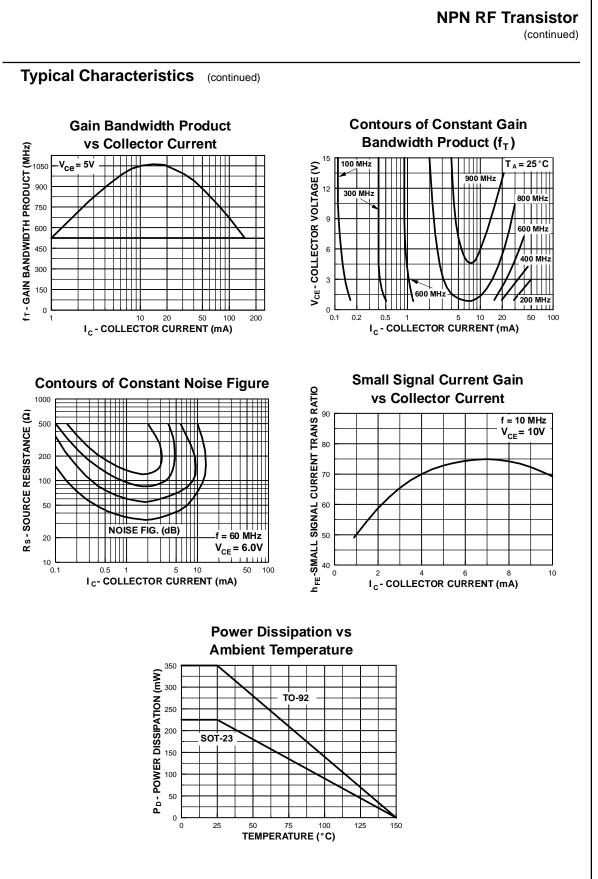
# FUNCTIONAL TEST

G <sub>pe</sub>	Amplifier Power Gain	$V_{CB} = 12 \text{ V}, \text{ I}_{C} = 6.0 \text{ mA},$ f = 200 MHz	15	dB
Po	Power Output	$V_{CB} = 15 \text{ V}, I_{C} = 8.0 \text{ mA},$ f = 500 MHz	30	mW
η	Collector Efficiency	$V_{CB} = 15 \text{ V}, \text{ I}_{C} = 8.0 \text{ mA},$ f = 500 MHz	25	%

\*Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%

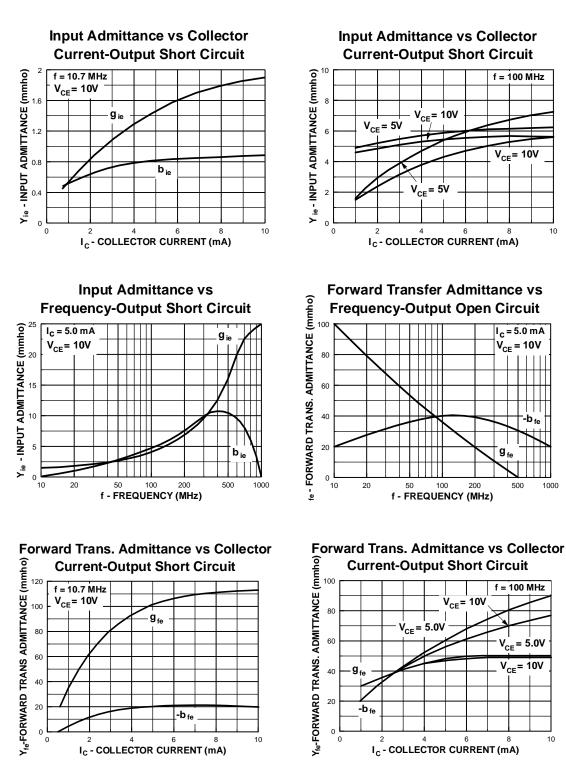
NPN RF Transistor (continued)











PN918 / MMBT918

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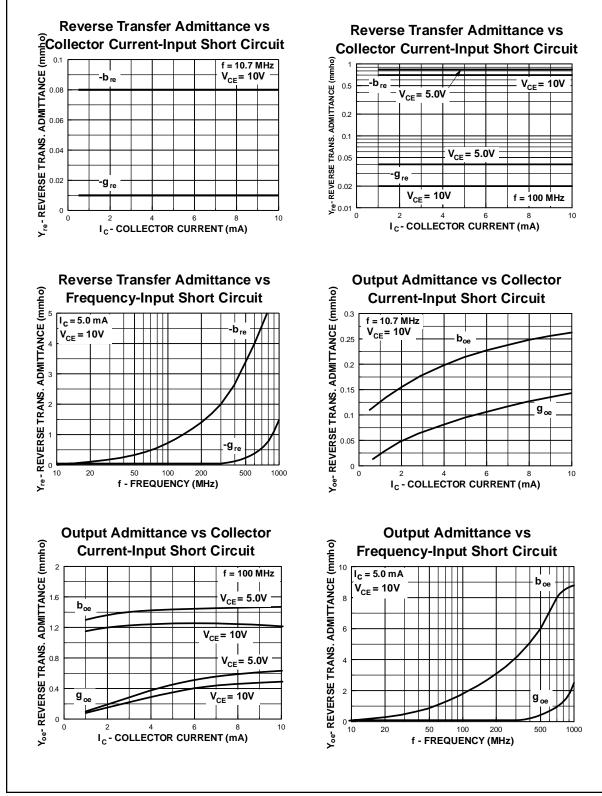
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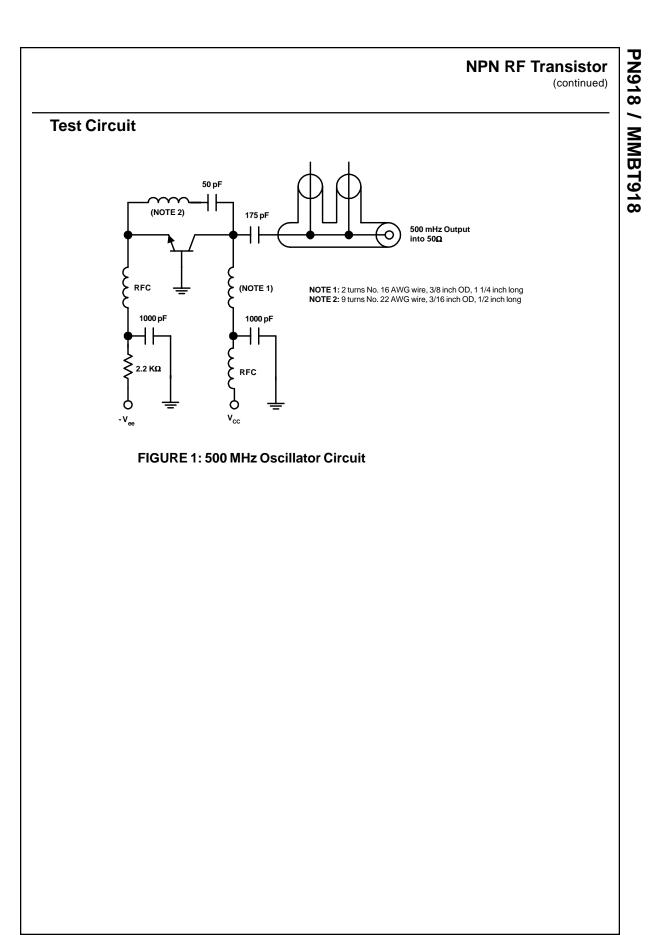
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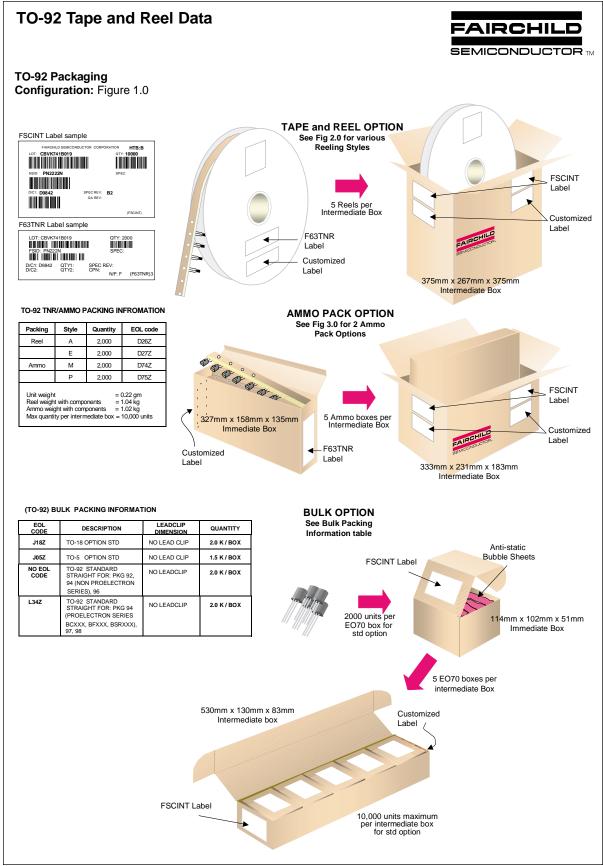
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NPN RF Transistor

### Common Emitter Y Parameters vs. Frequency (continued)

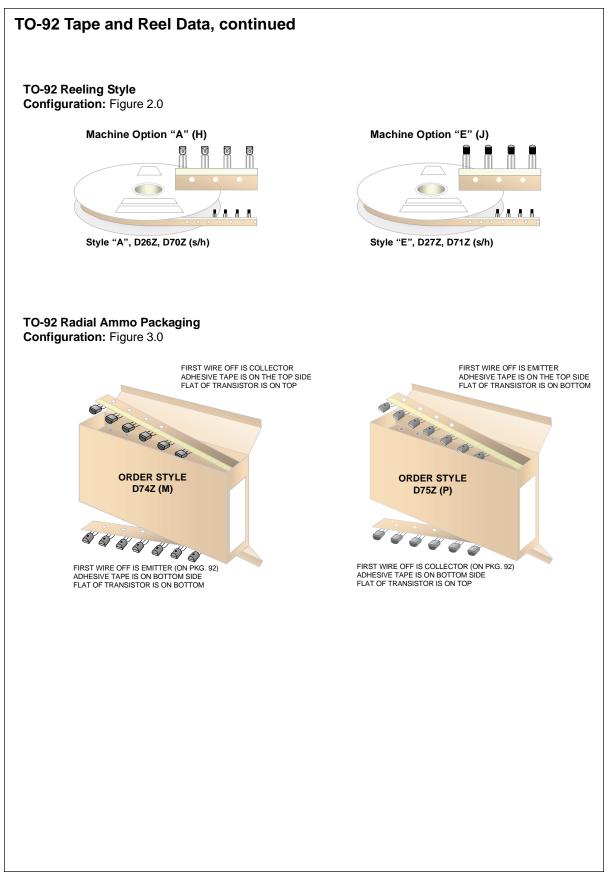




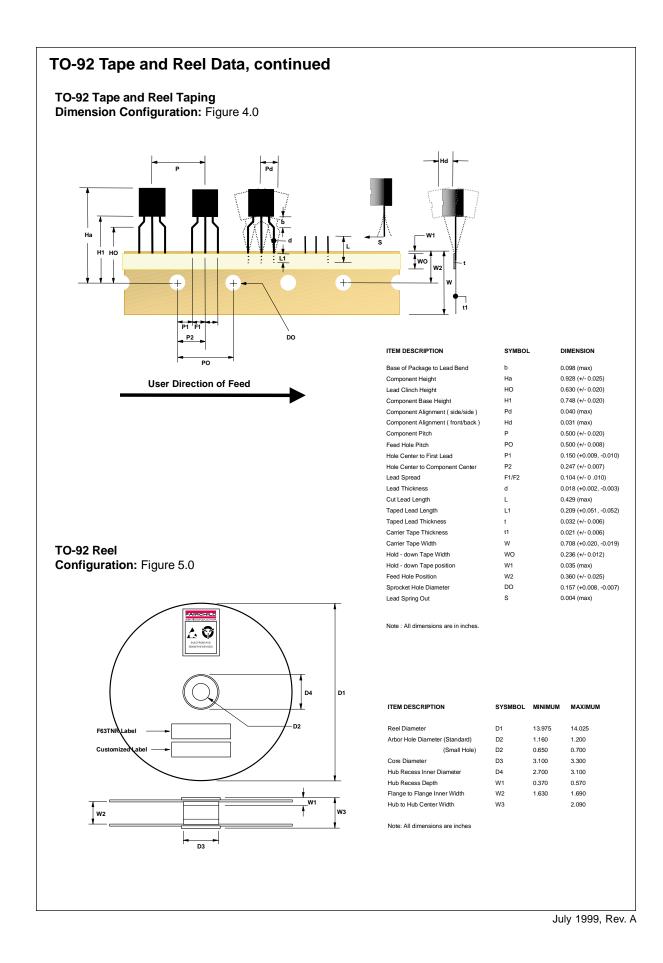


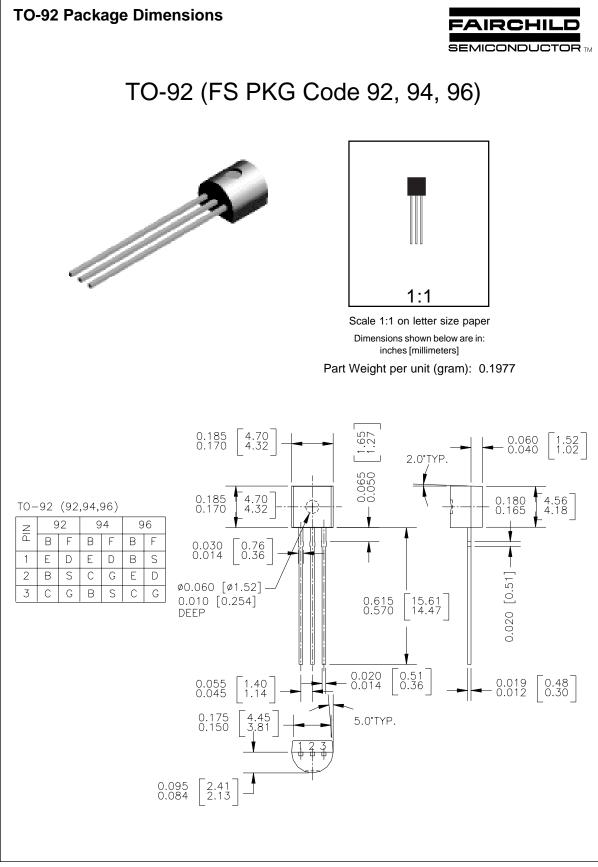
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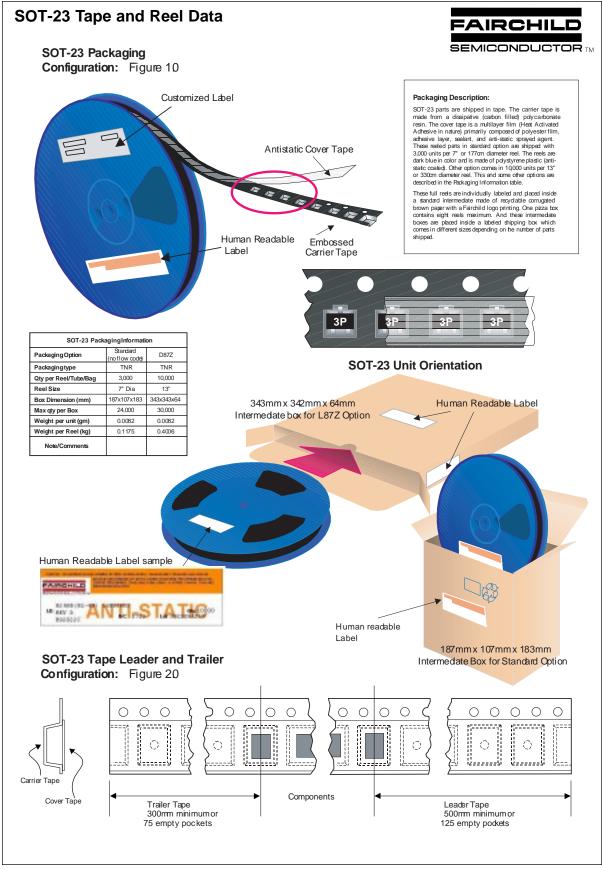
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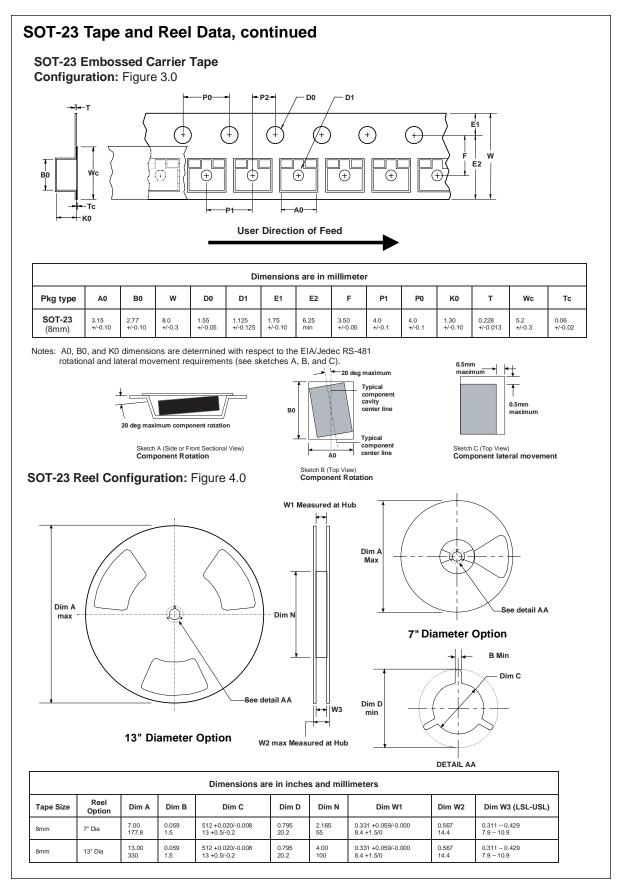
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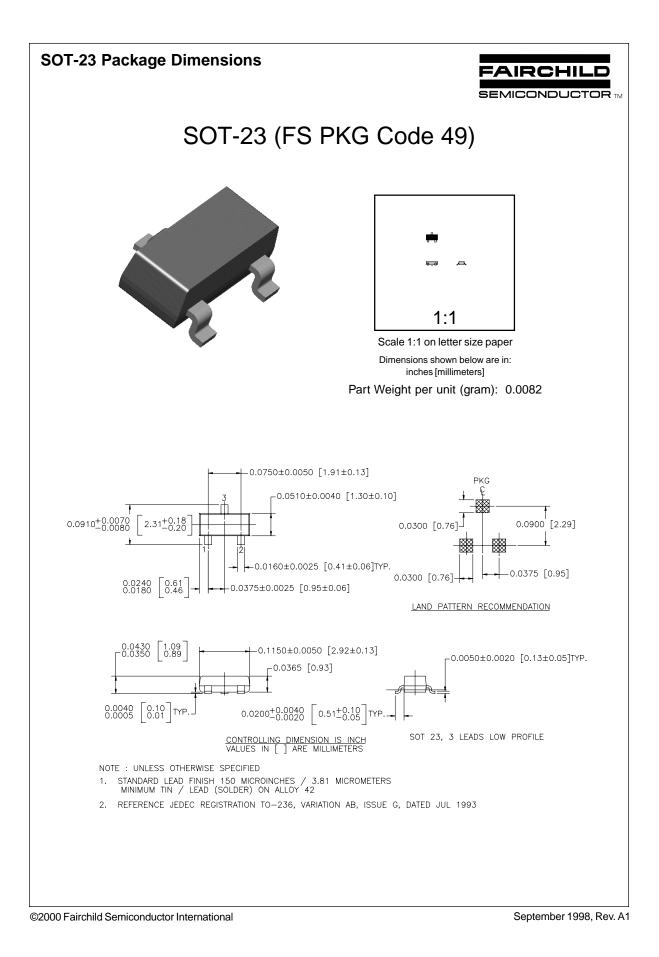


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